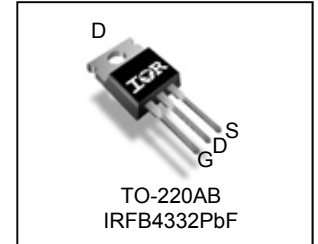
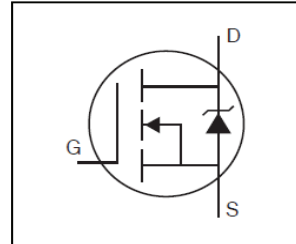


HEXFET® Power MOSFET

**Feature**

- Advanced Process Technology
- Key Parameters Optimized for PDP Sustain, Energy Recovery and Pass Switch Applications
- Low  $E_{PULSE}$  Rating to Reduce Power Dissipation in PDP Sustain, Energy Recovery and Pass Switch Applications
- Low  $Q_G$  for Fast Response
- High Repetitive Peak Current Capability for Reliable Operation
- Short Fall & Rise Times for Fast Switching
- 175°C Operating Junction Temperature for Improved Ruggedness
- Repetitive Avalanche Capability for Robustness and Reliability

Key Parameters		
$V_{DS\ min}$	250	V
$V_{DS(Avalanche)\ typ.}$	300	V
$R_{DS(on)\ typ.\ @\ 10V}$	29	mΩ
$T_J\ max$	175	°C



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFB4332PbF	TO-220	Tube	50	IRFB4332PbF

**Description**

This HEXFET® Power MOSFET is specifically designed for Sustain; Energy Recovery & Pass switch applications in Plasma Display Panels. This MOSFET utilizes the latest processing techniques to achieve low on-resistance per silicon area and low EPULSE rating. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications.

**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$V_{GS}$	Gate-to-Source Voltage	± 30	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	60	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	42	
$I_{DM}$	Pulsed Drain Current ①	230	
$I_{RP} @ T_C = 100^\circ C$	Repetitive Peak Current ⑤⑥	120	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	390	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	200	W
	Linear Derating Factor	2.6	W/°C
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf·in (1.1N·m)	

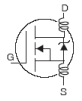
**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	0.38	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

Notes ① through ⑥ are on page 2.

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

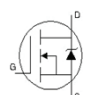
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	250	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	170	—	mV/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	29	33	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 35A
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.0	—	5.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
ΔV <sub>GS(th)</sub> /ΔT <sub>J</sub>	Gate Threshold Voltage Temp. Coefficient	—	-14	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 250V, V <sub>GS</sub> = 0V
		—	—	1.0	mA	V <sub>DS</sub> = 250V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Trans conductance	100	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 35A
Q <sub>g</sub>	Total Gate Charge	—	99	150	nC	V <sub>DD</sub> = 125V, I <sub>D</sub> = 35A, V <sub>GS</sub> = 10V <sup>③</sup>
Q <sub>gd</sub>	Gate-to-Drain Charge	—	35	—		
t <sub>st</sub>	Shoot Through Blocking Time	100	—	—	ns	V <sub>DD</sub> = 200V, V <sub>GS</sub> = 15V, R <sub>G</sub> = 4.7Ω
E <sub>PULSE</sub>	Energy per Pulse	—	520	—	μJ	L = 220nH, C = 0.3μF, V <sub>GS</sub> = 15V V <sub>DS</sub> = 200V, R <sub>G</sub> = 5.1Ω, T <sub>J</sub> = 25°C
		—	920	—		L = 220nH, C = 0.3μF, V <sub>GS</sub> = 15V V <sub>DS</sub> = 200V, R <sub>G</sub> = 5.1Ω, T <sub>J</sub> = 100°C
C <sub>iss</sub>	Input Capacitance	—	5860	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	530	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	130	—		f = 1.0MHz,
C <sub>oss eff.</sub>	Effective Output Capacitance	—	360	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 200V
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		


**Avalanche Characteristics**

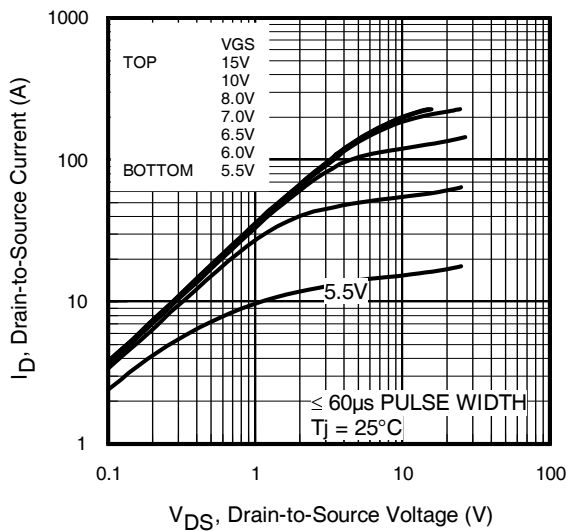
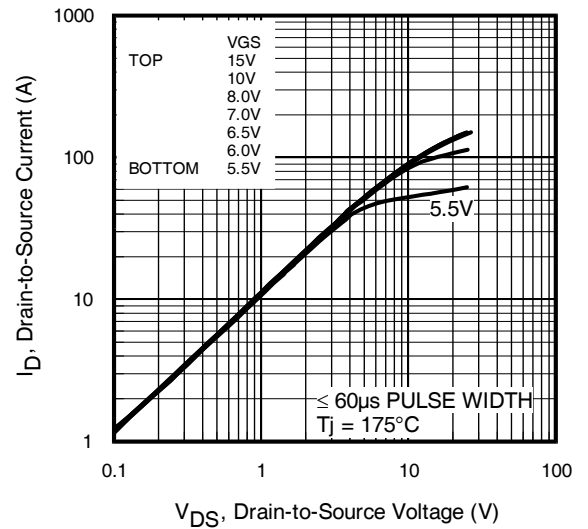
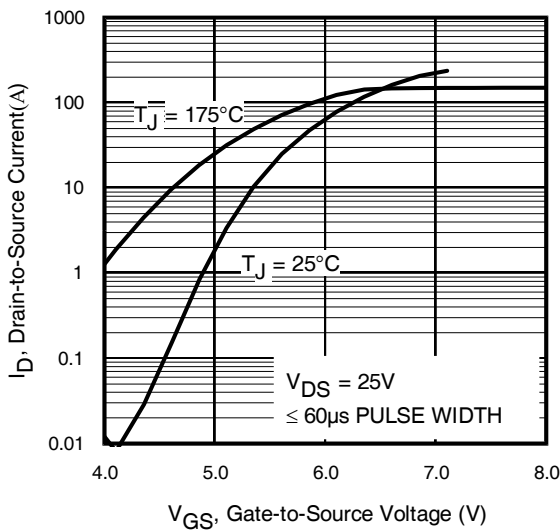
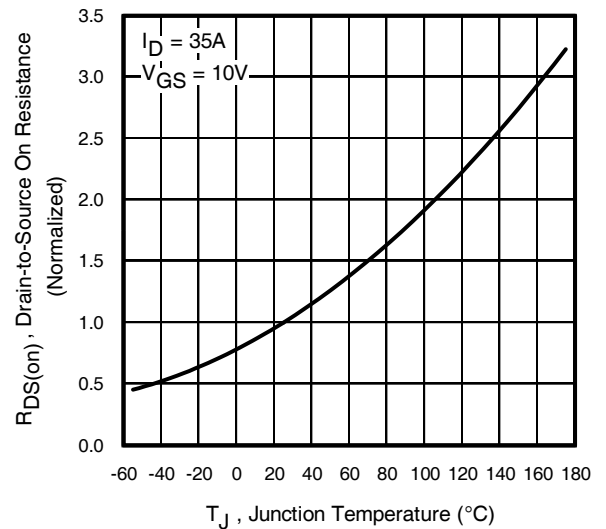
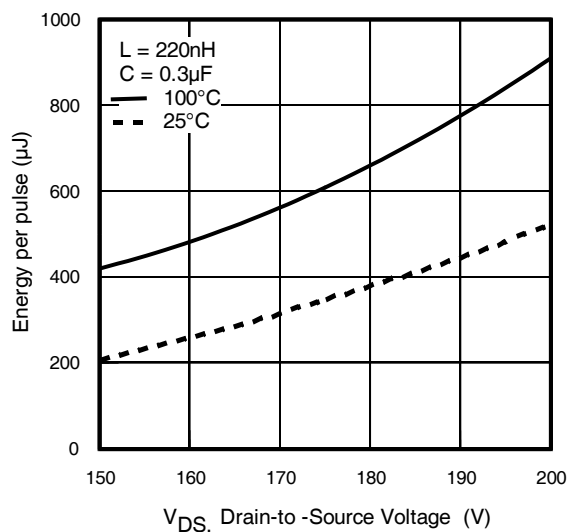
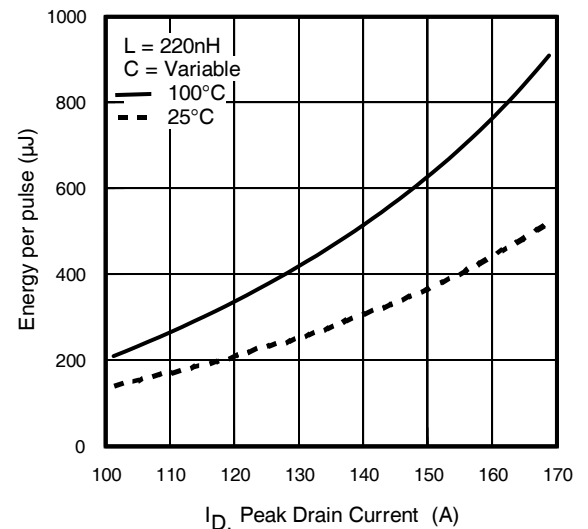
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>②</sup>	—	230	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy <sup>①</sup>	300	39	mJ
V <sub>DS (Avalanche)</sub>	Repetitive Avalanche Voltage <sup>①</sup>	—	—	V
I <sub>AS</sub>	Avalanche Current <sup>②</sup>	—	35	A

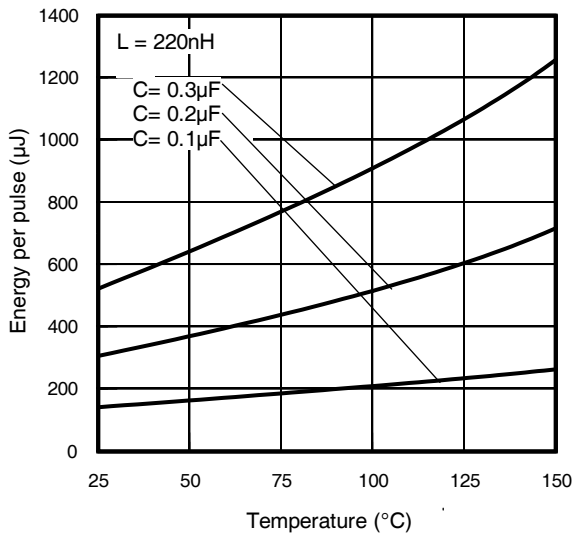
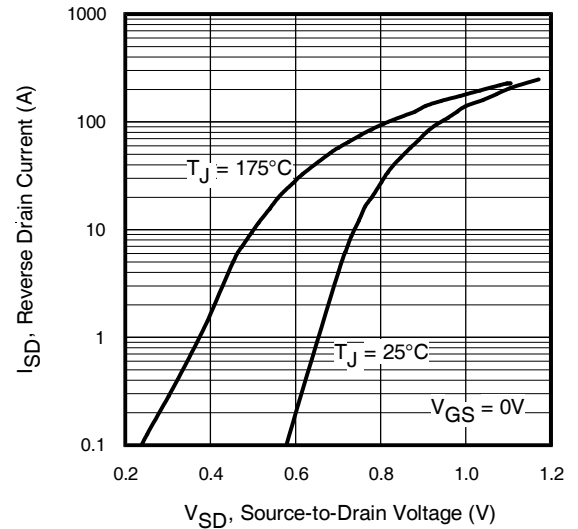
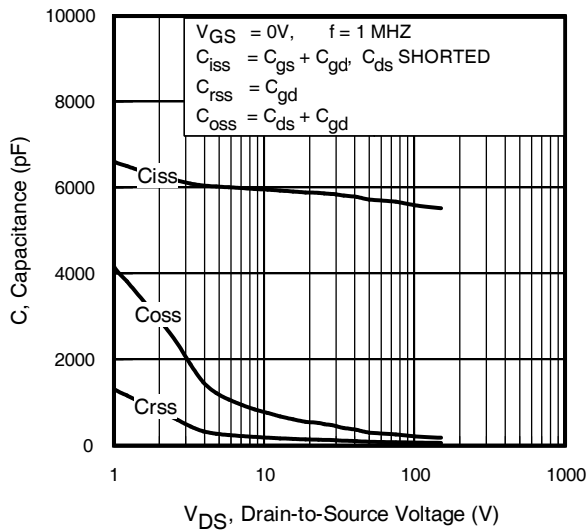
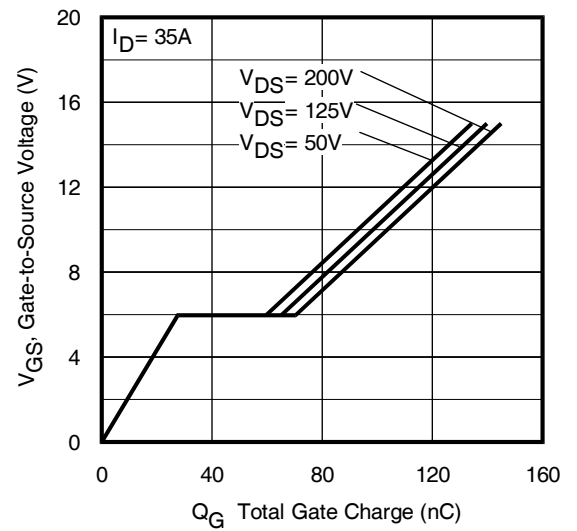
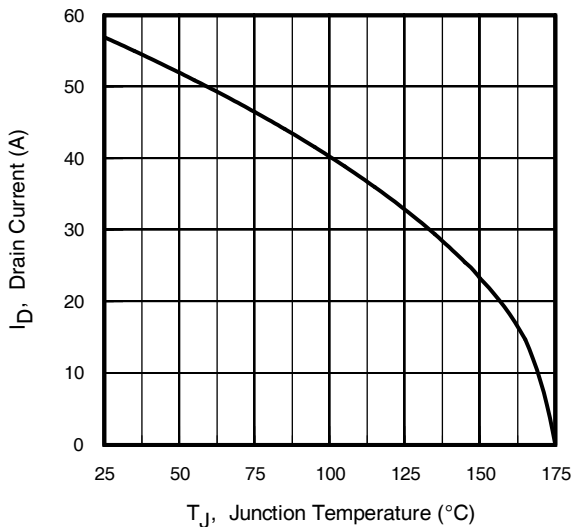
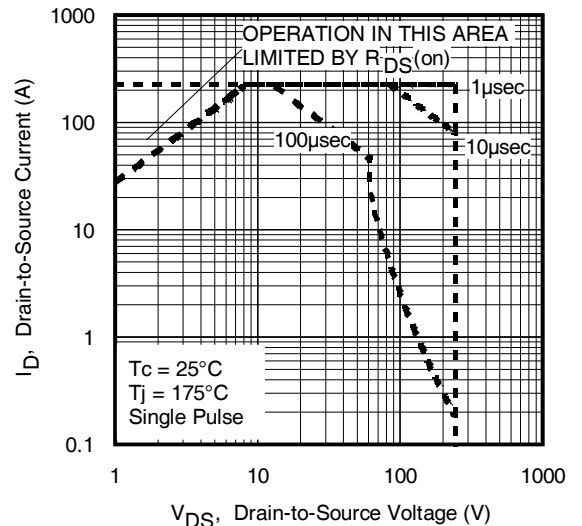
**Diode Characteristics**

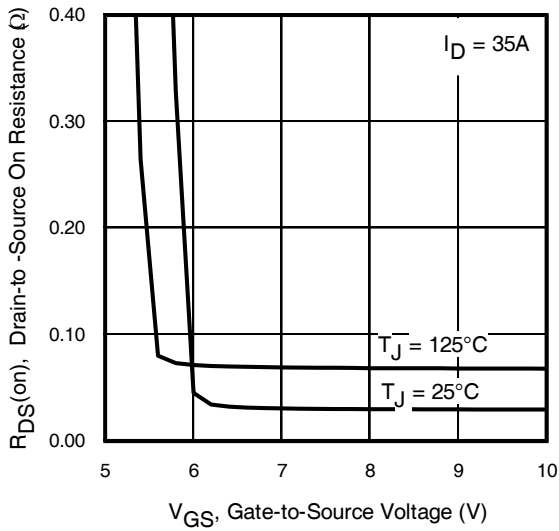
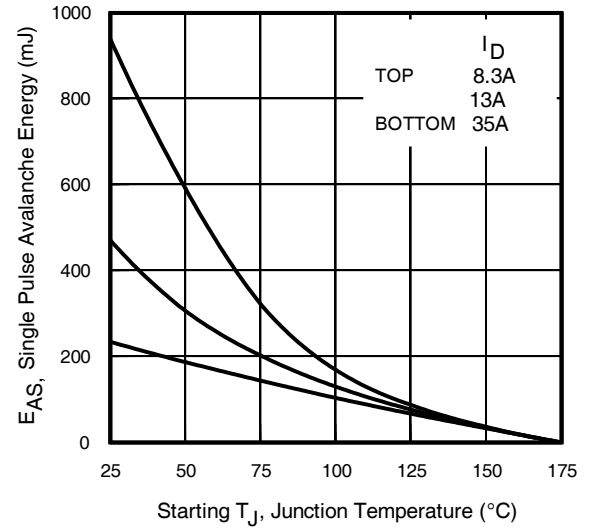
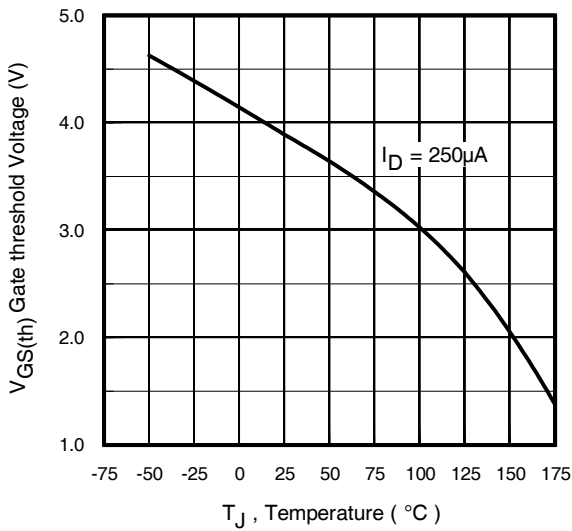
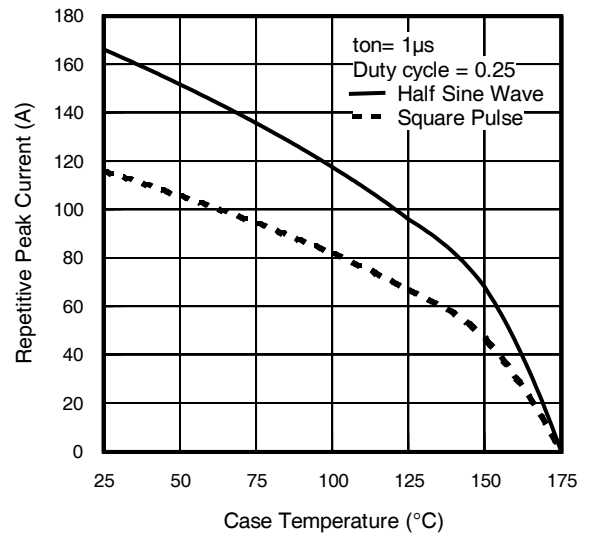
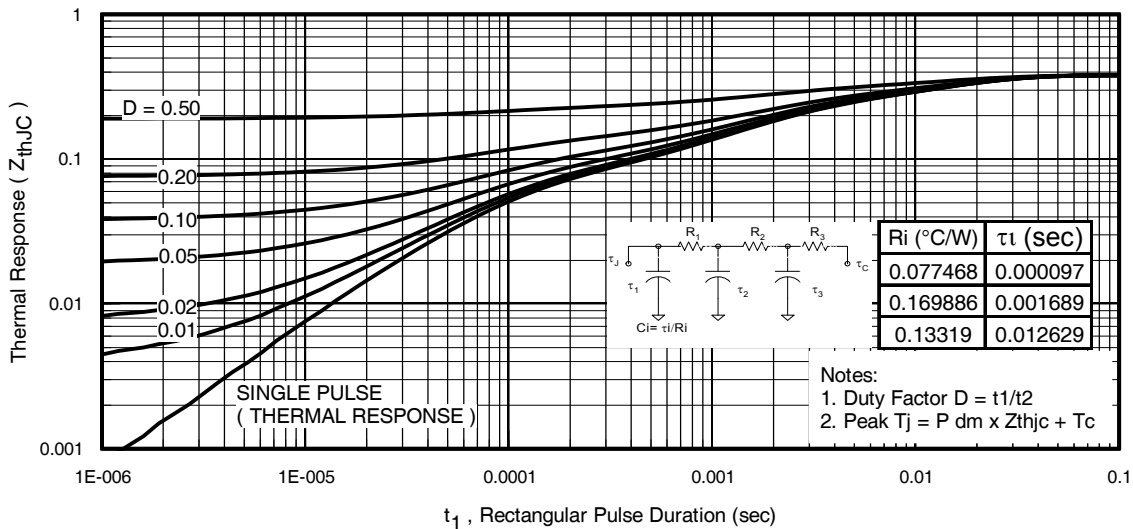
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub> @ T <sub>C</sub> = 25°C	Continuous Source Current (Body Diode)	—	—	60	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) <sup>①</sup>	—	—	230		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 35A, V <sub>GS</sub> = 0V <sup>③</sup>
t <sub>rr</sub>	Reverse Recovery Time	—	190	290	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 35A, V <sub>DD</sub> = 50V
Q <sub>rr</sub>	Reverse Recovery Charge	—	820	1230	nC	di/dt = 100A/μs <sup>③</sup>

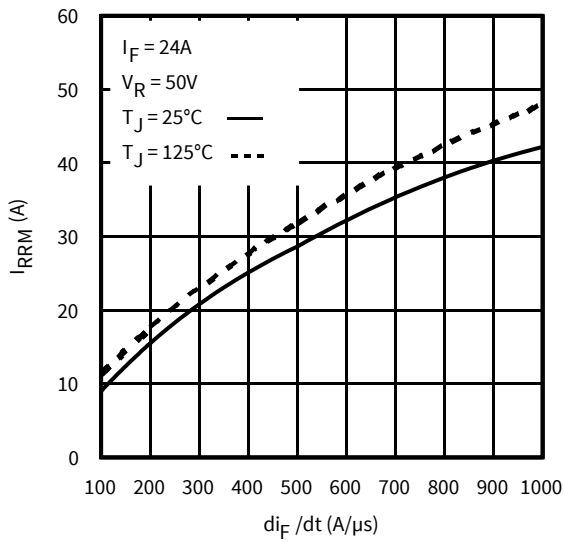
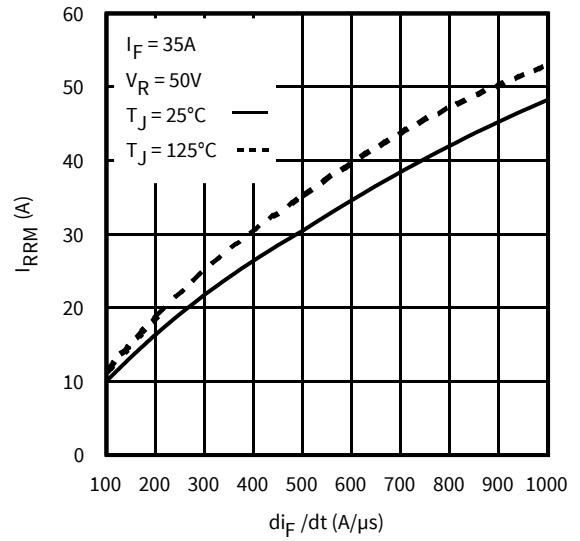
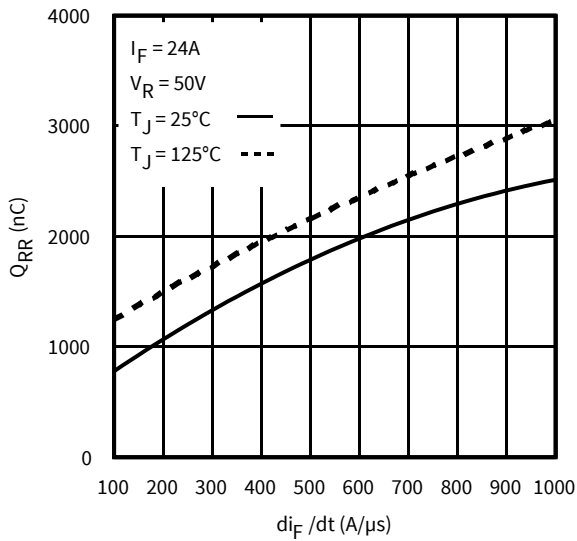
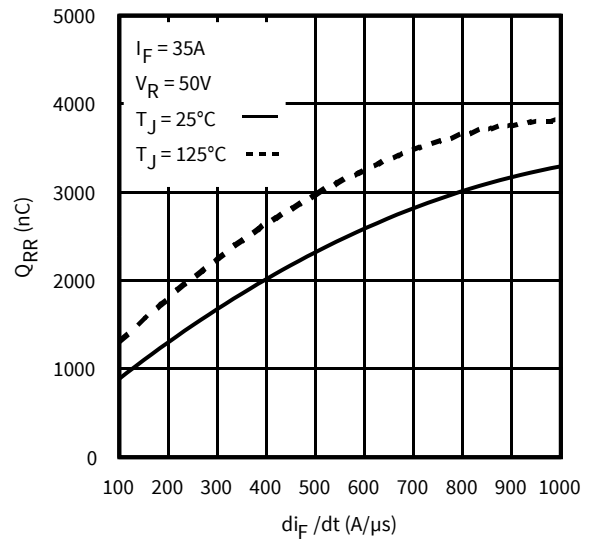

**Notes:**

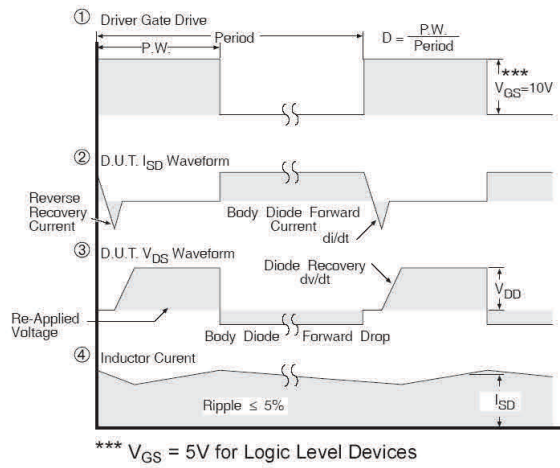
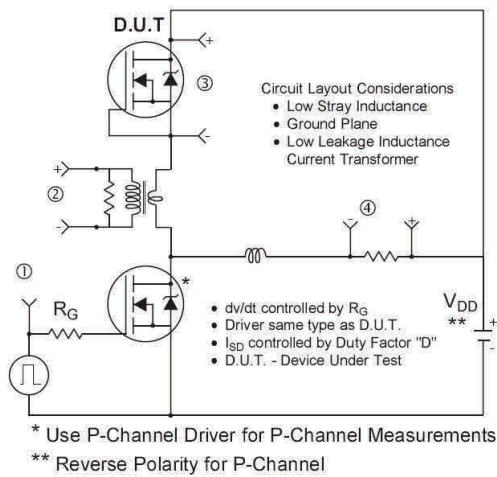
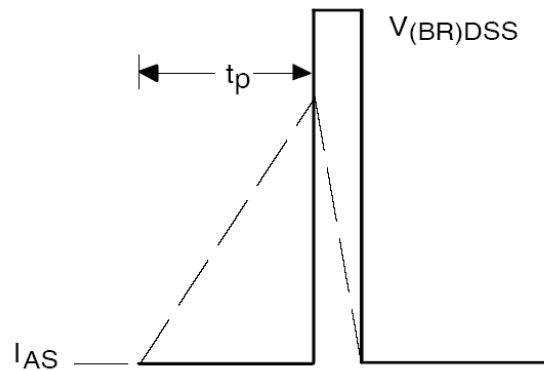
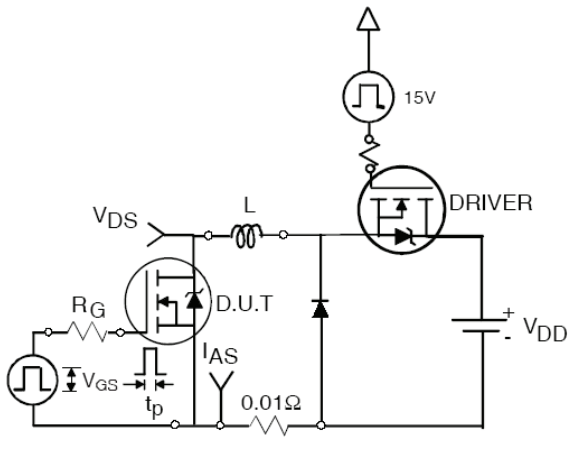
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② starting T<sub>J</sub> = 25°C, L = 0.39mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 35A.
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ④ R<sub>θ</sub> is measured at T<sub>J</sub> of approximately 90°C.
- ⑤ Half sine wave with duty cycle = 0.25, ton=1μsec.
- ⑥ Applicable to Sustain and Energy Recovery applications.

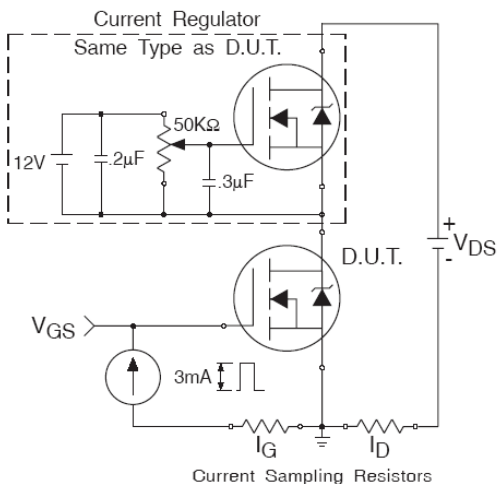
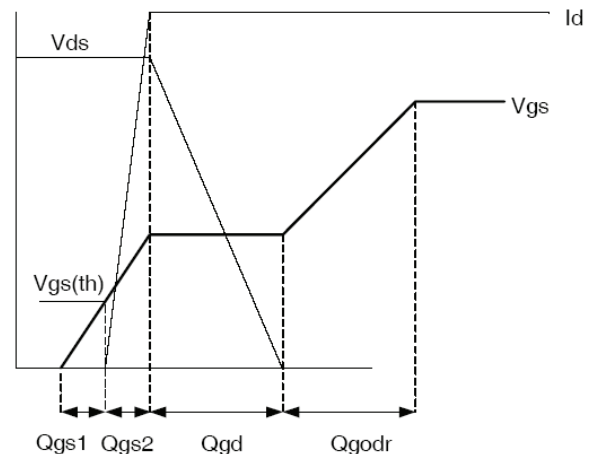

**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Normalized On-Resistance vs. Temperature**

**Fig 5. Typical  $E_{PULSE}$  vs. Drain-to-Source Voltage**

**Fig 6. Typical  $E_{PULSE}$  vs. Drain Current**

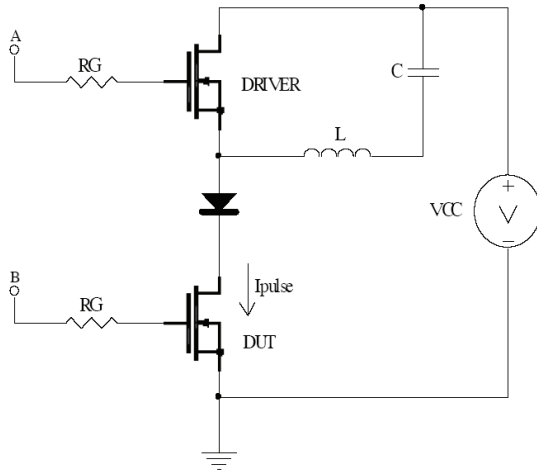
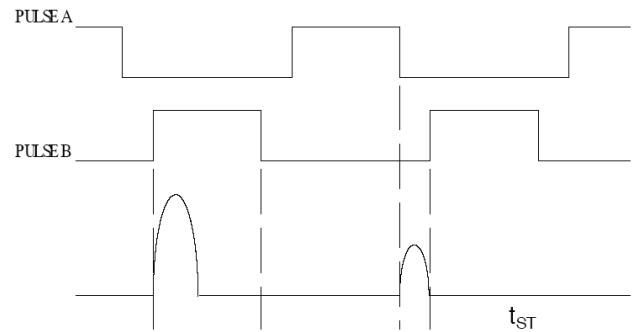
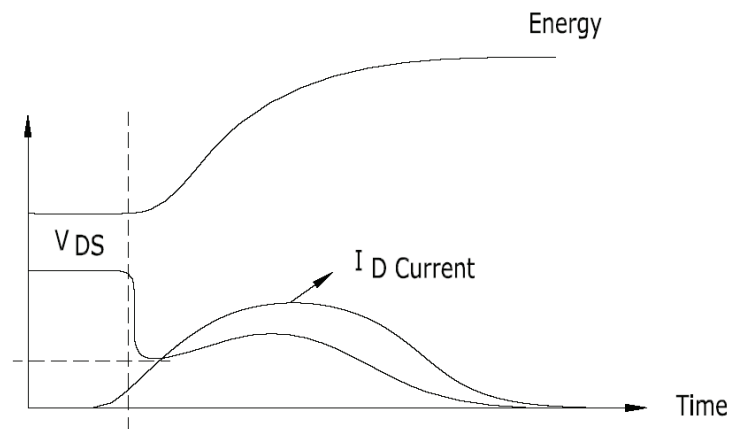

**Fig 7.** Typical EPULSE vs. Temperature

**Fig 8.** Typical Source-Drain Diode Forward Voltage

**Fig 9.** Typical Capacitance vs. Drain-to-Source Voltage

**Fig 10.** Typical Gate Charge vs. Gate-to-Source Voltage

**Fig 11.** Maximum Drain Current vs. Case Temperature

**Fig 12.** Maximum Safe Operating Area


**Fig 13.** On-Resistance Vs. Gate Voltage

**Fig 14.** Maximum Avalanche Energy Vs. Temperature

**Fig 15.** Threshold Voltage vs. Temperature

**Fig 16.** Typical Repetitive peak Current vs. Case temperature

**Fig 17.** Maximum Effective Transient Thermal Impedance, Junction-to-Case


**Fig. 18** - Typical Recovery Current vs.  $di/dt$ 

**Fig. 19** - Typical Recovery Current vs.  $di/dt$ 

**Fig. 20** - Typical Stored Charge vs.  $di/dt$ 

**Fig. 21** - Typical Stored Charge vs.  $di/dt$

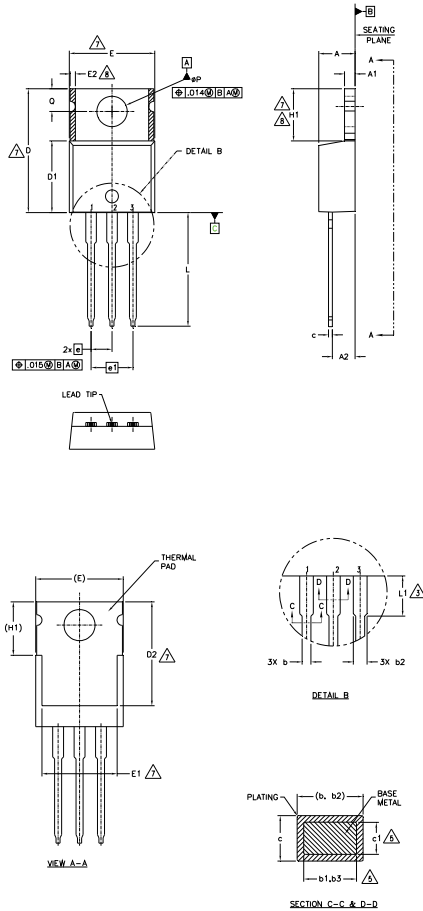

**Fig 18.** Diode Reverse Recovery Test Circuit for HEXFET® Power MOSFETs

**Fig 19a.** Unclamped Inductive Test Circuit

**Fig 19b.** Unclamped Inductive Waveforms

**Fig 20b.** Gate Charge Waveform

**Fig 20a.** Gate Charge Test Circuit


**Fig 21a.**  $t_{st}$  and EPULSE Test Circuit

**Fig 21b.**  $t_{st}$  Test Waveforms

**Fig 21c.** EPULSE Test Waveforms

**Fig 21c.** EPULSE Test Waveforms



**TO-220AB Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION : INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	1.14	1.40	.045	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		100 BSC		
e1	5.08 BSC		200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
$\phi P$	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

**LEAD ASSIGNMENTS**
**HEMFEET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

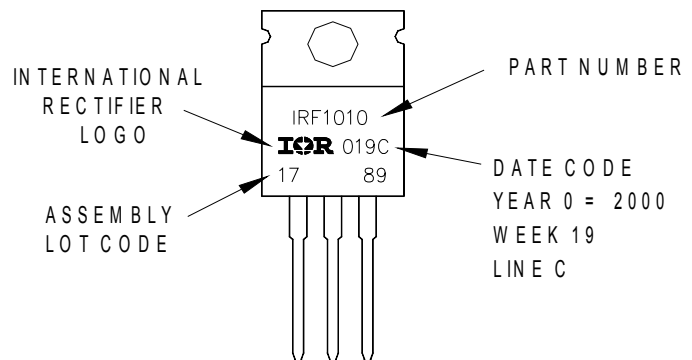
**DIODES**

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

**TO-220AB Part Marking Information**

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 2000  
 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position  
 indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

**Qualification Information**

<b>Qualification Level</b>	Industrial (per JEDEC JESD47F) †	
<b>Moisture Sensitivity Level</b>	TO-220AB	N/A
<b>RoHS Compliant</b>	Yes	

† Applicable version of JEDEC standard at the time of product release.

**Revision History**

Date	Comments
10/24/2016	<ul style="list-style-type: none"> <li>Changed datasheet with Infineon logo - all pages.</li> <li>Corrected Absolute Maximum table-Storage Temperature range from “-40C” to “-55C” on page1.</li> <li>Corrected Package Outline on page 8.</li> <li>Added disclaimer on last page.</li> </ul>
01/11/2018	<ul style="list-style-type: none"> <li>Added typical “Irr”, “Qrr” curves (Fig 18 to Fig 21) on page 6.</li> </ul>
08/16/2019	<ul style="list-style-type: none"> <li>Correct typo on Rdson units from “Ω” to “mΩ”-page2</li> </ul>

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Trademarks updated November 2015

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**Edition 2016-04-19**

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**Document reference**  
**ifx1**

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